AO4403

30V P-Channel MOSFET

General Description

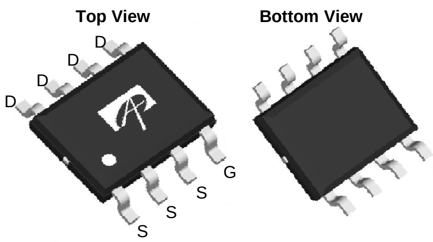
The AO4403 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

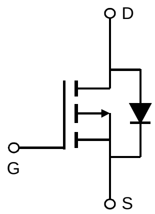
Product Summary

V_{DS}	-30V
I_D (at V_{GS}=-10V)	-6A
$R_{DS(ON)}$ (at V_{GS}=-10V)	< 48mΩ
$R_{DS(ON)}$ (at V_{GS} =-4.5V)	< 57mΩ
$R_{DS(ON)}$ (at V_{GS} =-2.5V)	< 80mΩ

100% UIS Tested
100% R_g Tested

SOIC-8





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current	T_A=25℃	I_D	-6	A
	T_A=70℃		-5	
Pulsed Drain Current [C]		I_{DM}	-30	
Avalanche Current [C]		I_{AS}, I_{AR}	18	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	16	mJ
Power Dissipation [B]	T_A=25℃	P_D	3.1	W
	T_A=70℃		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	31	40	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		59	75	℃/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	16	24	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V		-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V				-1	µA
			T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±12V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA		-0.5	-0.9	-1.3	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V		-30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-6A			40	48	mΩ
			T_J=125°C		60	72	
		V_{GS}=-4.5V, I_D=-4A			45	57	mΩ
		V_{GS}=-2.5V, I_D=-2A			60	80	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-6A			19		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V			-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current					-3.5	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz			645	780	pF
C_{oss}	Output Capacitance				80		pF
C_{rss}	Reverse Transfer Capacitance				55		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		4	7.8	12	Ω
SWITCHING PARAMETERS							
Q_g(4.5V)	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-15V, I_D=-6A			7		nC
Q_{gs}	Gate Source Charge				1.5		nC
Q_{gd}	Gate Drain Charge				2.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=2.5Ω, R_{GEN}=6Ω			6.5		ns
t_r	Turn-On Rise Time				3.5		ns
$t_{D(off)}$	Turn-Off DelayTime				41		ns
t_f	Turn-Off Fall Time				9		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-6A, dI/dt=100A/µs			11		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-6A, dI/dt=100A/µs			3.5		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

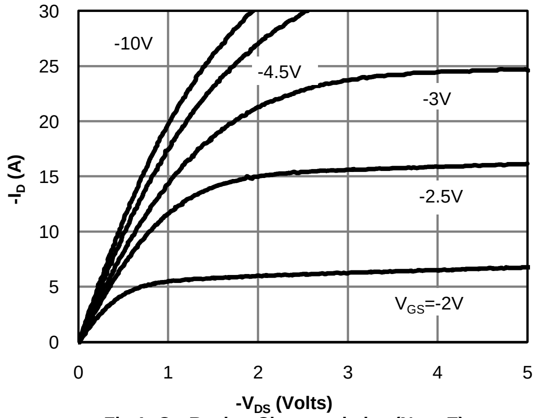


Fig 1: On-Region Characteristics (Note E)

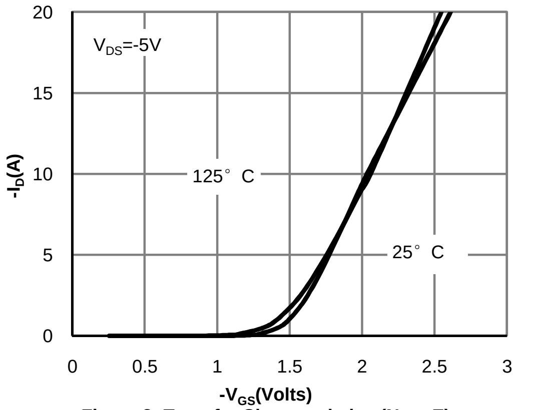


Figure 2: Transfer Characteristics (Note E)

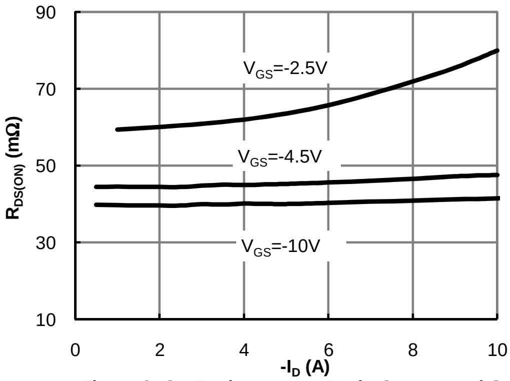


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

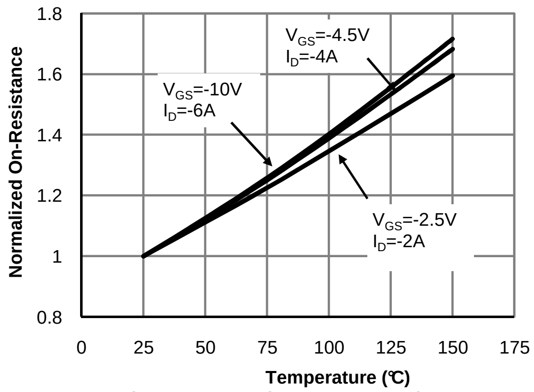


Figure 4: On-Resistance vs. Junction Temperature (Note E)

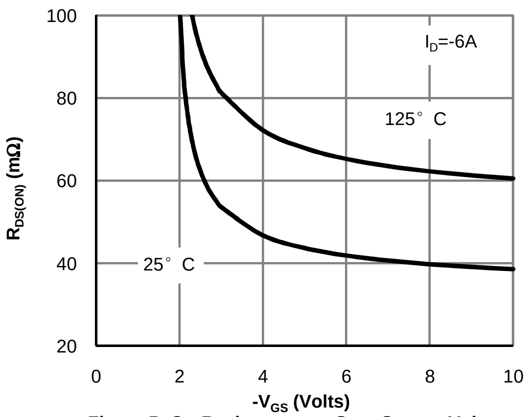


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

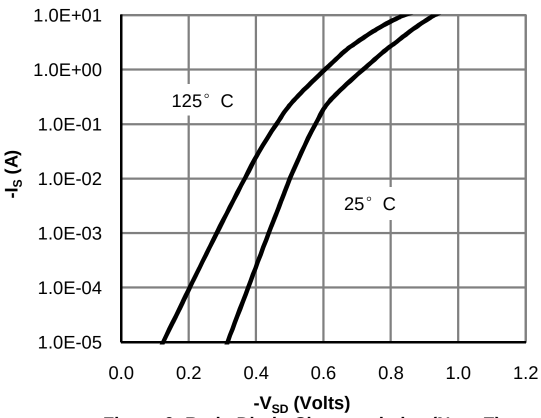


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

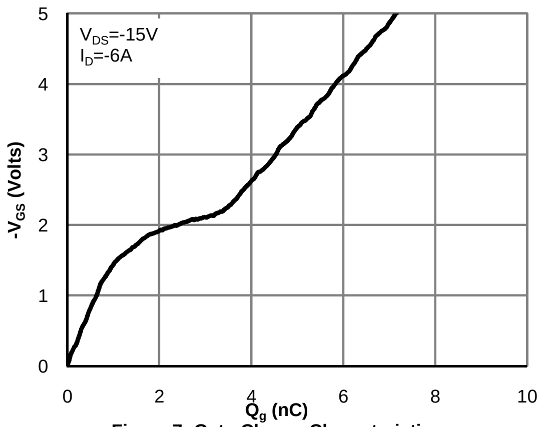


Figure 7: Gate-Charge Characteristics

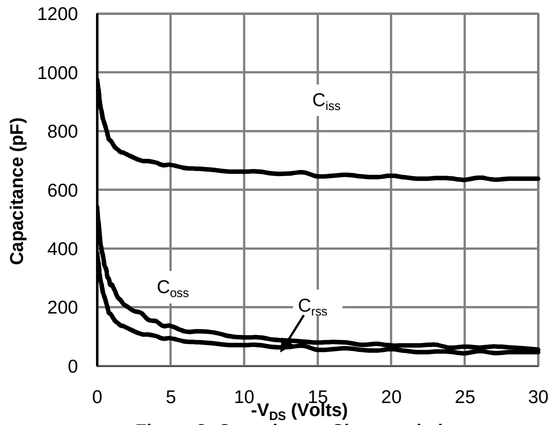


Figure 8: Capacitance Characteristics

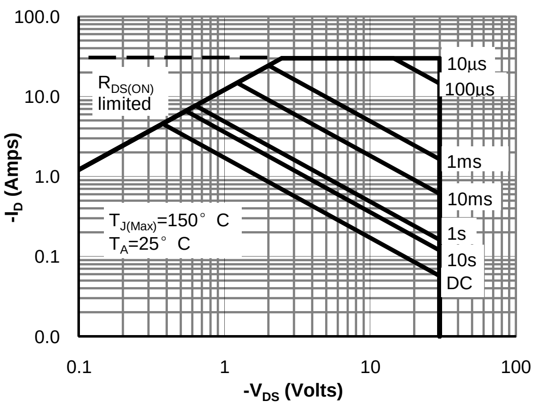


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

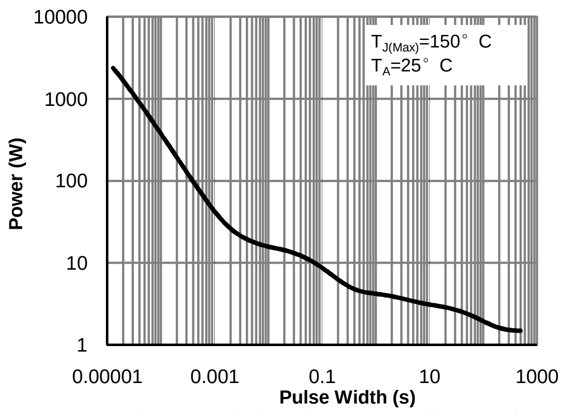


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

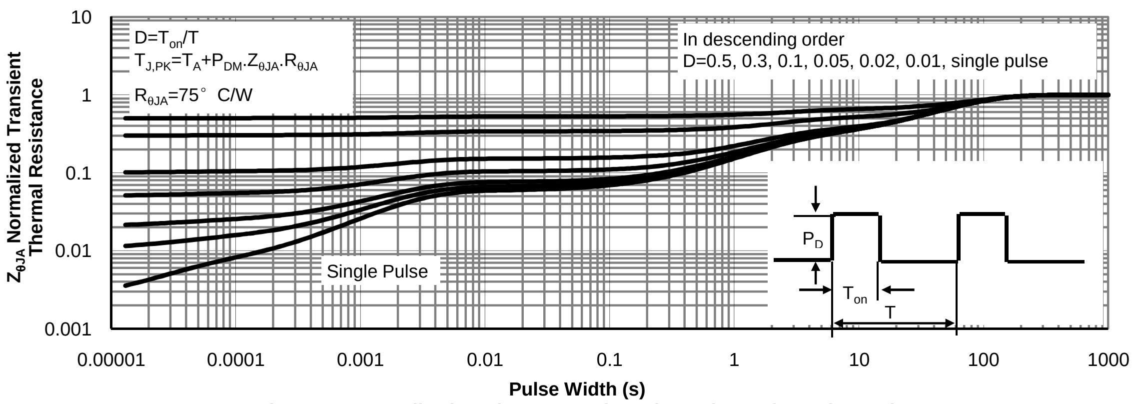
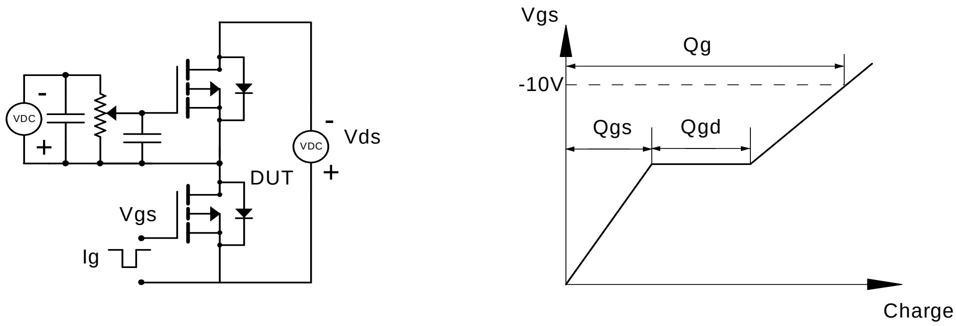
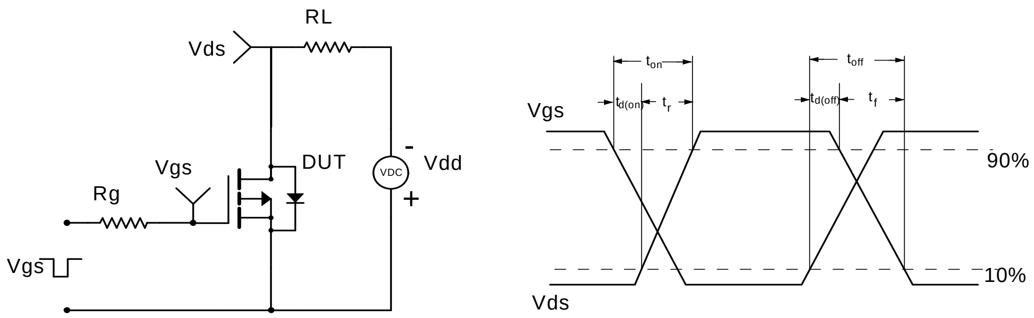


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

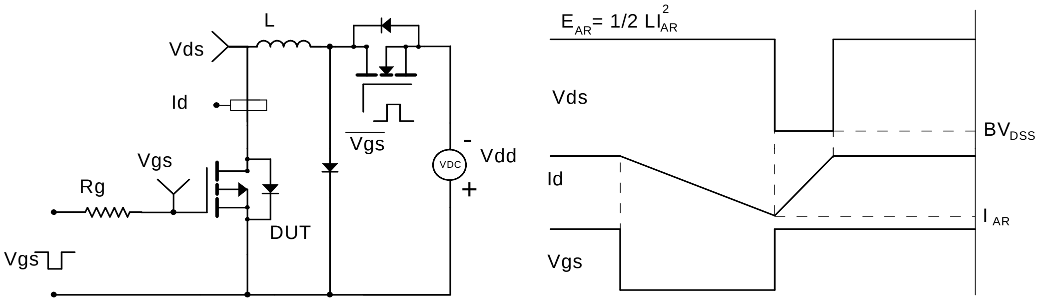
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms